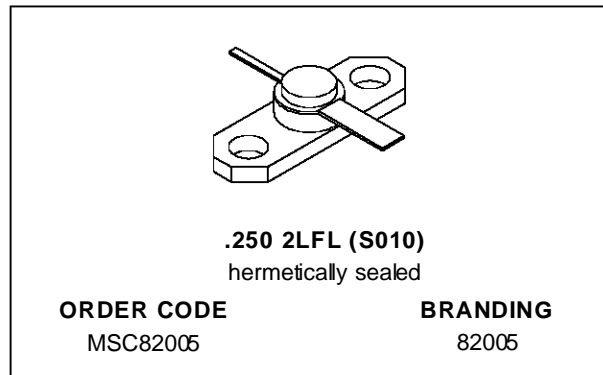


RF & MICROWAVE TRANSISTORS GENERAL PURPOSE AMPLIFIER APPLICATIONS

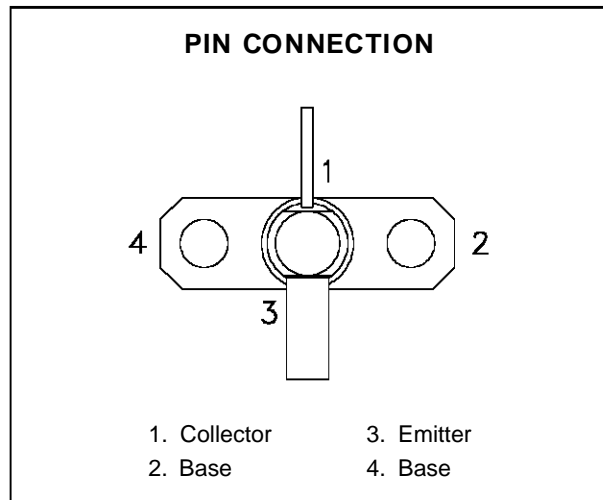
- EMITTER BALLASTED
- VSWR CAPABILITY $\infty:1$ @ RATED CONDITIONS
- REFRACTORY/GOLD METALLIZATION
- HERMETIC STRIPAC[®] PACKAGE
- $P_{OUT} = 5.0$ W MIN. WITH 7.0 dB GAIN @ 2.0 GHz



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DESCRIPTION

The MSC82005 is a common base hermetically sealed silicon NPN microwave transistor utilizing a fishbone emitter ballasted geometry with a refractory/gold metallization system. This device is capable of withstanding an infinite load VSWR at any phase angle under rated conditions. The MSC82005 was designed for Class C amplifier applications in the 1.0 - 2.0 GHz frequency range.



ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation*	29	W
I_C	Device Current*	1.0	A
V_{CC}	Collector-Supply Voltage*	35	V
T_J	Junction Temperature	200	$^{\circ}C$
T_{STG}	Storage Temperature	- 65 to +200	$^{\circ}C$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	6.0	$^{\circ}C/W$
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*Applies only to rated RF amplifier operation

MSC82005

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

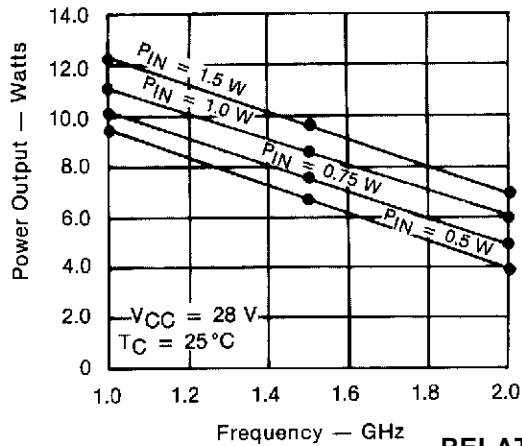
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 1mA	I _E = 0mA	45	—	—	V
BV _{EBO}	I _E = 1mA	I _C = 0mA	3.5	—	—	V
BV _{CER}	I _C = 5mA	R _{BE} = 10Ω	45	—	—	V
I _{CBO}	V _{CB} = 28V		—	—	2.5	mA
h _{FE}	V _{CE} = 5V	I _C = 500mA	15	—	120	—

DYNAMIC

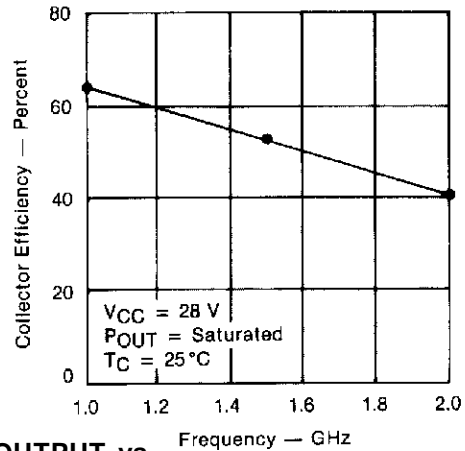
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 2.0 GHz	P _{IN} = 1.0 W	V _{CC} = 28 V	5.0	6.0	—	W
η _c	f = 2.0 GHz	P _{IN} = 1.0 W	V _{CC} = 28 V	35	40	—	%
G _P	f = 2.0 GHz	P _{IN} = 1.0 W	V _{CC} = 28 V	7.0	7.8	—	dB
C _{OB}	f = 1 MHz	V _{CB} = 28 V		—	—	10	pF

TYPICAL PERFORMANCE

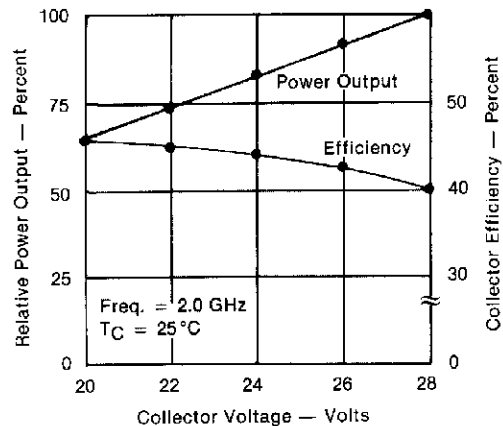
POWER OUTPUT vs FREQUENCY



COLLECTOR EFFICIENCY vs FREQUENCY



RELATIVE POWER OUTPUT vs COLLECTOR VOLTAGE

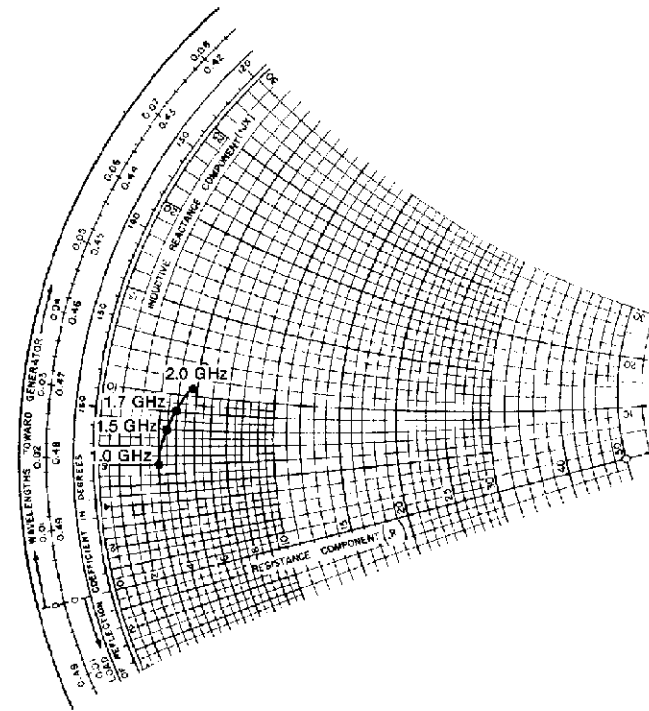


IMPEDANCE DATA

TYPICAL INPUT IMPEDANCE

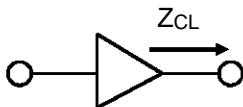


$P_{IN} = 1.0\text{ W}$
 $V_{CC} = 28\text{ V}$
 Normalized to 50 ohms

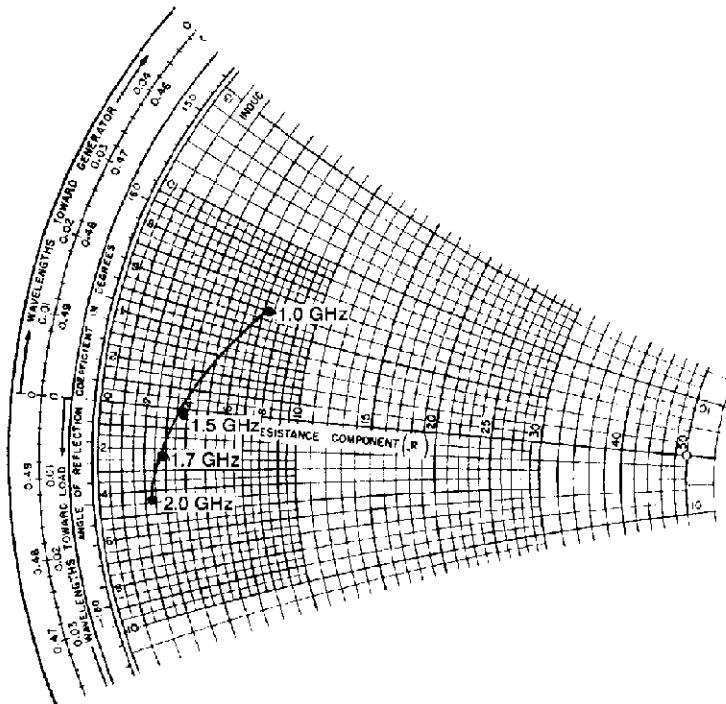


FREQ.	$Z_{IN} (\Omega)$	$Z_{CL} (\Omega)$
1.0 GHz	$3.0 + j 6.0$	$7.2 + j 6.0$
1.5 GHz	$3.5 + j 8.0$	$3.7 - j 0.2$
1.7 GHz	$4.0 + j 9.0$	$2.8 - j 2.3$
2.0 GHz	$4.8 + j 10.5$	$2.3 - j 4.5$

TYPICAL COLLECTOR LOAD IMPEDANCE



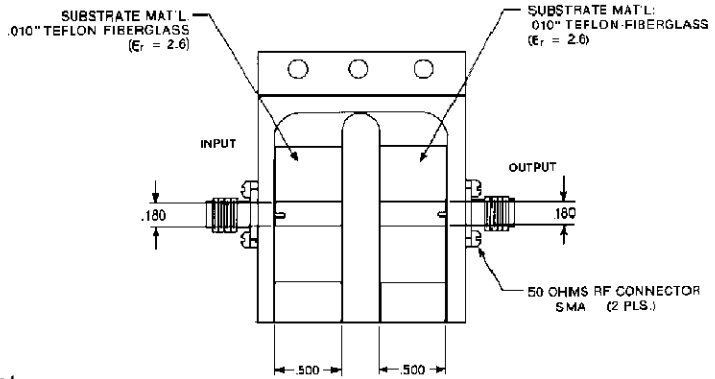
$P_{OUT} = \text{Saturated}$
 $V_{CC} = 28\text{ V}$
 Normalized to 50 ohms



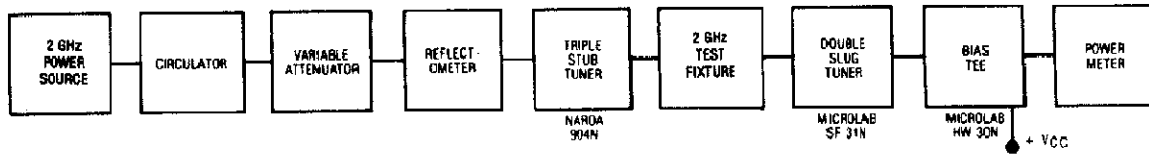
TEST CIRCUIT

Ref.: Dwg. No. C125518

All dimensions are in inches.
Frequency 2.0 GHz

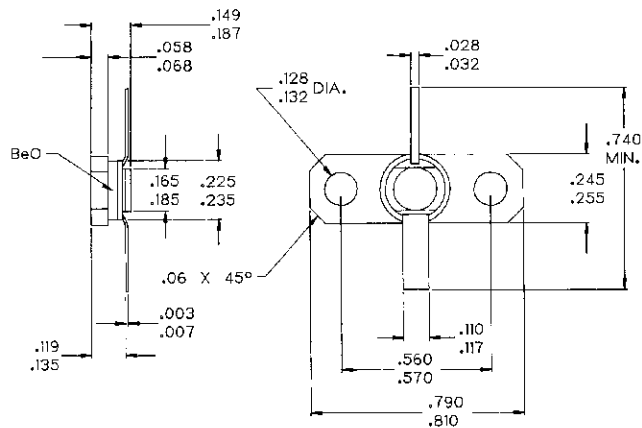


RF Amplifier Power Output Test



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.: J135021C



NOTES:
1. ALL TOLERANCE ± .010 EXCEPT WHERE NOTED;
DIMENSIONS IN INCHES.

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